

MC74HC367A

Hex 3-State Noninverting Buffer with Separate 2-Bit and 4-Bit Sections

High-Performance Silicon-Gate CMOS

The MC74HC367A is identical in pinout to the LS367. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device is arranged into 2-bit and 4-bit sections, each having its own active-low Output Enable. When either of the enables is high, the affected buffer outputs are placed into high-impedance states. The HC367A has noninverting outputs.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μ A
- High Noise Immunity Characteristic of CMOS Devices
- These are Pb-Free Devices

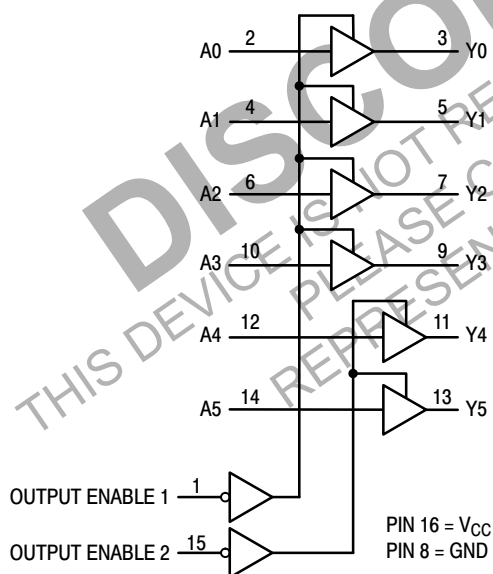


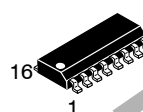
Figure 1. Logic Diagram



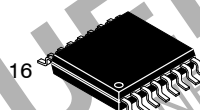
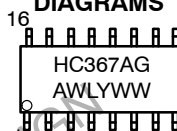
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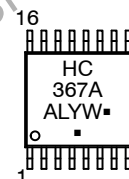
MARKING DIAGRAMS



SOIC-16
D SUFFIX
CASE 751B



TSSOP-16
DT SUFFIX
CASE 948F



A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT

OUTPUT ENABLE 1	1	16	V _{CC}
A0	2	15	OUTPUT ENABLE 2
Y0	3	14	A5
A1	4	13	Y5
Y1	5	12	A4
A2	6	11	Y4
Y2	7	10	A3
GND	8	9	Y3

FUNCTION TABLE

Inputs		Output
Enable 1, Enable 2	A	Y
L	L	L
L	H	H
H	X	Z

X = don't care

Z = high impedance

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MC74HC367A

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V_{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air, SOIC Package TSSOP Package	500 450	mW
T_{stg}	Storage Temperature	-65 to +150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	-55	+125	°C
t_r, t_f	Input Rise and Fall Time (Figure 2)	$V_{CC} = 2.0 \text{ V}$ 0 $V_{CC} = 3.0 \text{ V}$ 0 $V_{CC} = 4.5 \text{ V}$ 0 $V_{CC} = 6.0 \text{ V}$ 0	1000 600 500 400	ns

MC74HC367A

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				- 55 to 25°C	≤ 85°C	≤ 125°C	
V _{IH}	Minimum High-Level Input Voltage	V _{out} = V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low-Level Input Voltage	V _{out} = 0.1 V I _{out} ≤ 20 μA	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	V
V _{OH}	Minimum High-Level Output Voltage	V _{in} = V _{IH} I _{out} ≤ 20 μA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V _{in} = V _{IH} I _{out} ≤ 3.6 mA	3.0	2.48	2.34	2.20	
		I _{out} ≤ 6.0 mA	4.5	3.98	3.84	3.70	
		I _{out} ≤ 7.8 mA	6.0	5.48	5.34	5.20	
V _{OL}	Maximum Low-Level Output Voltage	V _{in} = V _{IL} I _{out} ≤ 20 μA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V _{in} = V _{IL} I _{out} ≤ 3.6 mA	3.0	0.26	0.33	0.40	
		I _{out} ≤ 6.0 mA	4.5	0.26	0.33	0.40	
		I _{out} ≤ 7.8 mA	6.0	0.26	0.33	0.40	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I _{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GND	6.0	± 0.5	± 5.0	± 10	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	6.0	4	40	160	μA

MC74HC367A

AC ELECTRICAL CHARACTERISTICS ($C_L = 50$ pF, Input $t_r = t_f = 6$ ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			- 55 to 25°C	≤ 85°C	≤ 125°C	
t_{PLH} , t_{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	120 60 24 20	150 75 30 26	180 90 36 31	ns
t_{PLZ} , t_{PHZ}	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 5)	2.0 3.0 4.5 6.0	175 90 35 30	220 110 44 37	265 135 53 45	ns
t_{PZL} , t_{PZH}	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 5)	2.0 3.0 4.5 6.0	190 95 38 32	240 120 48 21	285 150 57 48	ns
t_{TLH} , t_{THL}	Maximum Output Transition Time, Any Output (Figures 2 and 4)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns
C_{in}	Maximum Input Capacitance	—	10	10	10	pF
C_{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)	—	15	15	15	pF

C _{PD}	Power Dissipation Capacitance (Per Buffer)	Typical @ 25°C, V _{CC} = 5.0 V	pF
		60	

SWITCHING WAVEFORMS

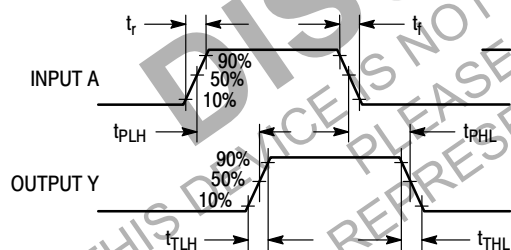


Figure 2.

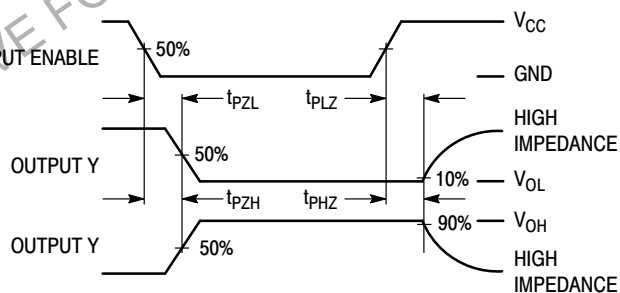
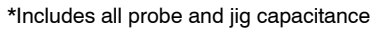


Figure 3.

TEST CIRCUITS



*Includes all probe and jig capacitance

The diagram illustrates a 6-to-1 multiplexer circuit. It features six input buffers, each receiving a common input signal 'A'. The outputs of these buffers are connected to two 3-input NAND gates. The first NAND gate's inputs are the outputs of the first three buffers, and its output is connected to the drain of an n-channel MOSFET. The second NAND gate's inputs are the outputs of the last three buffers, and its output is connected to the drain of a p-channel MOSFET. The gates of both MOSFETs are connected to a common control signal 'Y'. The source of the n-channel MOSFET is connected to ground, and the source of the p-channel MOSFET is connected to V_{CC} . The common drain connection of the two MOSFETs provides the multiplexer output 'Y'. A dashed box encloses the internal logic components (NAND gates and MOSFETs), while the buffers are shown outside. Labels include 'TO OTHER BUFFERS' at the top, 'ONE OF 6 BUFFERS' near the top right, 'V_{CC}' at the top right, and 'OUTPUT ENABLE' at the bottom left.

Figure 6. Logic Detail

Device	Package	Shipping [†]
MC74HC367ADG	SOIC–16 (Pb–Free)	48 Units / Rail
MC74HC367ADR2G	SOIC–16 (Pb–Free)	2500 Tape & Reel
MC74HC367ADTG	TSSOP–16 (Pb–Free)	96 Units / Tube
MC74HC367ADTR2G	TSSOP–16 (Pb–Free)	2500 Tape & Reel

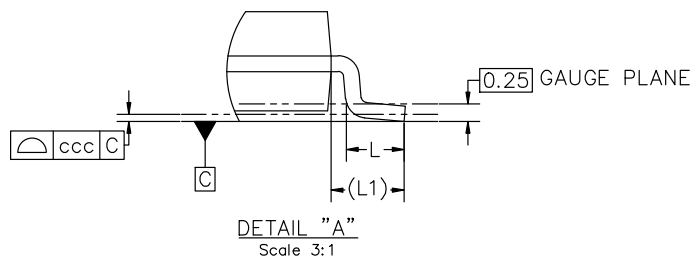
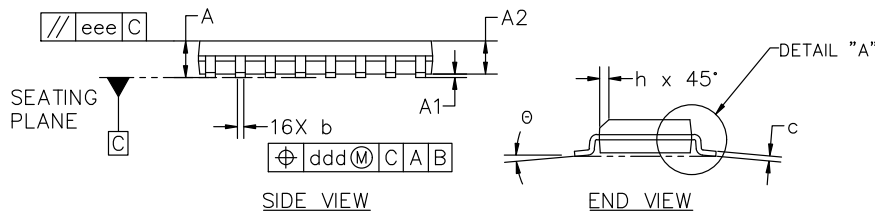
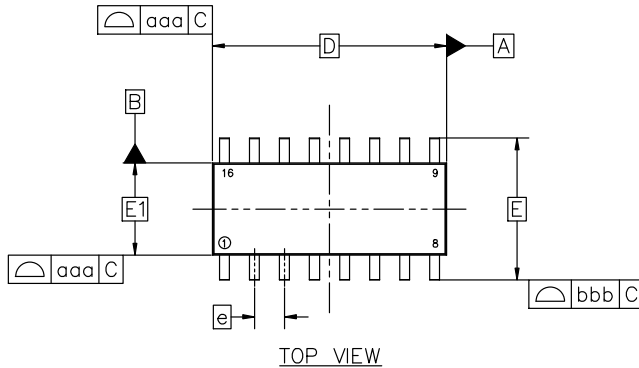
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SOIC-16 9.90x3.90x1.37 1.27P
CASE 751B
ISSUE M

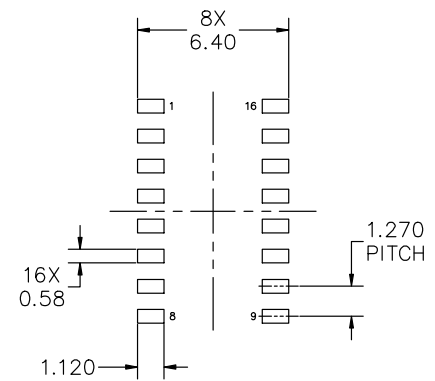
DATE 18 OCT 2024

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
5. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION.



MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.10	0.18	0.25
A2	1.25	1.37	1.50
b	0.35	0.42	0.49
c	0.19	0.22	0.25
D	9.90 BSC		
E	6.00 BSC		
E1	3.90 BSC		
e	1.27 BSC		
h	0.25	---	0.50
L	0.40	0.83	1.25
L1	1.05 REF		
theta	0°	---	7°
TOLERANCE OF FORM AND POSITION			
aaa	0.10		
bbb	0.20		
ccc	0.10		
ddd	0.25		
eee	0.10		



RECOMMENDED MOUNTING FOOTPRINT

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AND MOUNTING TECHNIQUES REFERENCE
MANUAL, SOLDERM/D

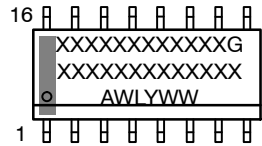
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CASE 751B
ISSUE M

DATE 18 OCT 2024

GENERIC
MARKING DIAGRAM*



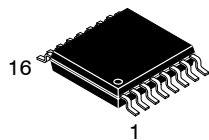
XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

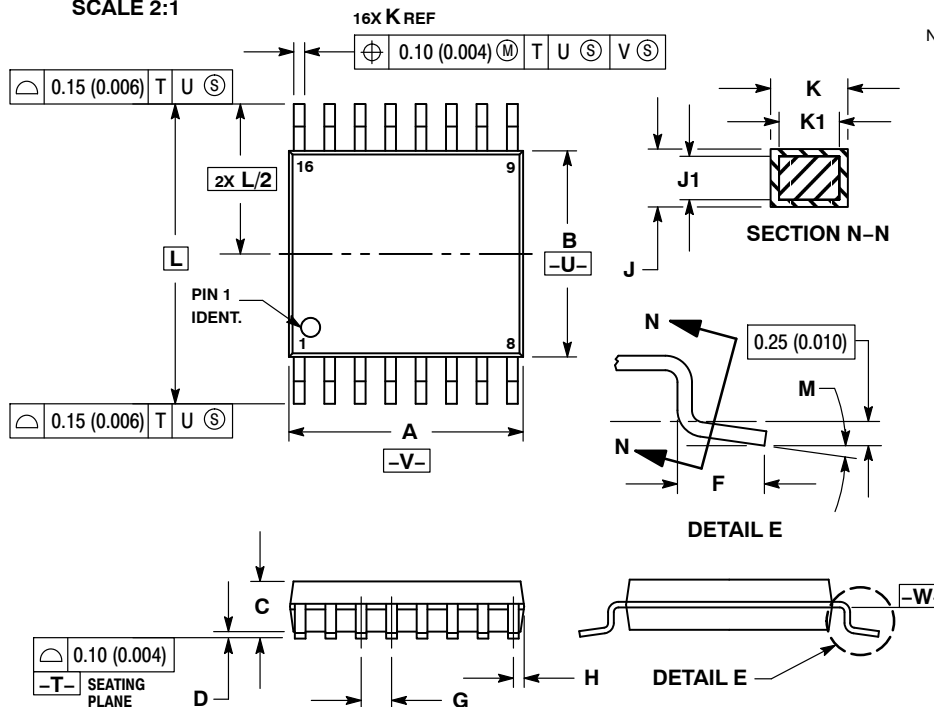
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STYLE 5: PIN 1. DRAIN, DYE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. DRAIN, #3 6. DRAIN, #3 7. DRAIN, #4 8. DRAIN, #4 9. GATE, #4 10. SOURCE, #4 11. GATE, #3 12. SOURCE, #3 13. GATE, #2 14. SOURCE, #2 15. GATE, #1 16. SOURCE, #1	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. CATHODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE 15. ANODE 16. ANODE	STYLE 7: PIN 1. SOURCE N-CH 2. COMMON DRAIN (OUTPUT) 3. COMMON DRAIN (OUTPUT) 4. GATE P-CH 5. COMMON DRAIN (OUTPUT) 6. COMMON DRAIN (OUTPUT) 7. COMMON DRAIN (OUTPUT) 8. SOURCE P-CH 9. SOURCE P-CH 10. COMMON DRAIN (OUTPUT) 11. COMMON DRAIN (OUTPUT) 12. COMMON DRAIN (OUTPUT) 13. GATE N-CH 14. COMMON DRAIN (OUTPUT) 15. COMMON DRAIN (OUTPUT) 16. SOURCE N-CH	

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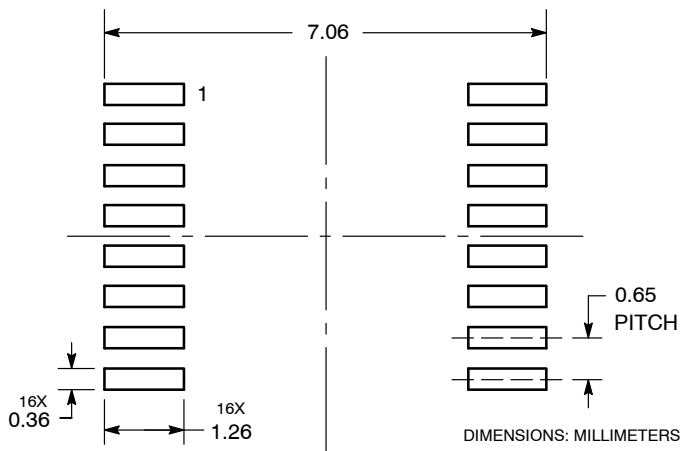

TSSOP-16 WB
CASE 948F
ISSUE B

DATE 19 OCT 2006

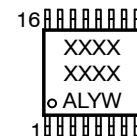

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

**RECOMMENDED
SOLDERING FOOTPRINT***


*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**GENERIC
MARKING DIAGRAM***


XXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
G or ■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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